

IN THE ABSTRACT

Page 137, line 4, change "leak" to --leakage--.

IN THE CLAIMS

Please cancel claims 1-9 without prejudice.

Please add new claims 14-15 as follows:

--14. A method of manufacturing a semiconductor device in which there are first and second types of transistors formed on a single semiconductor substrate, comprising the steps of:

(a) selectively forming a field oxide film on a main surface of said semiconductor substrate to thereby define first and second regions in which said first and said second types of transistors are formed;

(b) forming an oxide film on said first and said second ^{active} regions; and

(c) forming a control electrode of a polysilicon layer ^{on said} ~~ons and~~ first and said second regions,

wherein said step (c) includes the steps of:

(c-1) introducing an impurity of the same conductivity as a source/drain layer into said polysilicon layer within said first active region at a relatively low dose n1; and

(c-2) introducing said impurity into said polysilicon layer within said second active region at a relatively high dose n2 while introducing nitrogen into a lower portion of said polysilicon layer within said second active region at a dose n3.

15. The method of manufacturing a semiconductor device of claim ¹⁴ ~~13~~, wherein said dose n1 is $5 \times 10^{14}/\text{cm}^2$, said dose n2 is $5 \times 10^{15}/\text{cm}^2$, and said dose n3 is $1 \times 10^{15}/\text{cm}^2$.--